



30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} Max	I _D Max @ T _A = +25°C
-30V	2.4Ω @ $V_{GS} = -10V$	-400mA
-30 V	$4\Omega @ V_{GS} = -4.5V$	-300mA

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Load Switch
- Portable Applications
- Power Management Functions

Features

- Low On-Resistance
- Ultra-Small Surfaced Mount Package
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

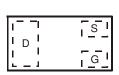
- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ^{@4}
- Weight: 0.001 grams (Approximate)



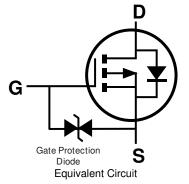




Bottom View



Top View



Ordering Information (Note 4)

Part Number	Reel Size (inches)	Quantity per Reel
DMP32D5SFB-7B	7	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Top View
Bar Denotes Gate and Source Side

XH = Product Type Marking Code



Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	-30	V	
Gate-Source Voltage		V _{GSS}	±25	V	
Continuous Drain Current (Note 5)	V _{GS} = -10V	$T_A = +25$ °C $T_A = +70$ °C	I _D	-400 -300	mA
Continuous Drain Current (Note 6)	V _{GS} = -10V	$T_A = +25$ °C $T_A = +70$ °C	I _D	-500 -400	mA
Pulsed Drain Current (Note 5)		I _{DM}	-1	A	
Maximum Body Diode Continuous Current (Note 6)		Is	-800	mA	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Dawer Dissination	(Note 5)	0	0.5	w	
Total Power Dissipation	(Note 6)	P_{D}	1.2		
Thermal Resistance, Junction to Ambient	(Note 5)	0	255	°C/W	
Thermal nesistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	108		
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	-30	-	-	V	$V_{GS} = 0V$, $I_D = -1mA$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	-	-1	μΑ	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(TH)}$	-1.3	-	-2.3	٧	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance				2.4	Ω	$V_{GS} = -10V, I_D = -200mA$	
Static Dialii-Source Off-Nesistance	R _{DS(ON)}	-	-	4		$V_{GS} = -4.5V, I_{D} = -200mA$	
Diode Forward Voltage	V_{SD}	-	0.8	1.2	V	$V_{GS} = 0V, I_{S} = -300mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	-	51	100	рF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	-	11	20	pF		
Reverse Transfer Capacitance	C _{rss}	-	9	20	pF	T = 1.0WII IZ	
Total Gate Charge	Qg	-	0.62	2	nC	V _{GS} = -4.5V	
Total Gate Charge	Q_g	-	1.25	4	nC	$V_{DS} = -10V$,	
Gate-Source Charge	Q_{gs}	-	0.16	0.5	nC	$V_{GS} = -10V$ $I_{D} = -200mA$	
Gate-Drain Charge	Q _{gd}	-	0.21	0.5	nC		
Turn-On Delay Time	t _{D(ON)}	-	4.3	10	ns		
Turn-On Rise Time	t _R	-	7.7	15	ns	$V_{DS} = -15V, I_{D} = -500mA$	
Turn-Off Delay Time	t _{D(OFF)}	-	31.9	60	ns	$V_{GS} = -10V$, $R_G = 1\Omega$	
Turn-Off Fall Time	t _F	-	17.8	40	ns		

Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
- 7 .Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.





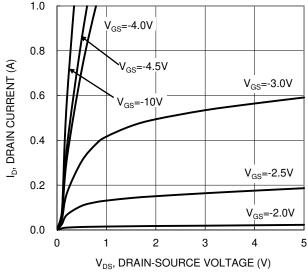


Figure 1. Typical Output Characteristic

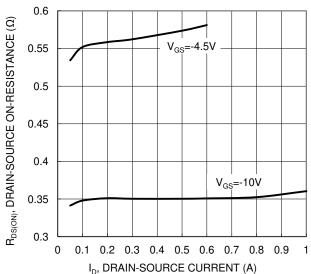


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

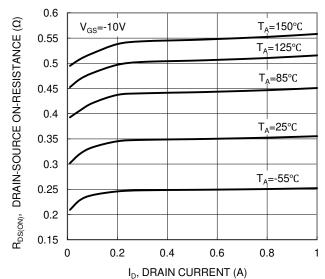
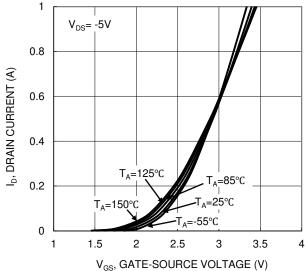
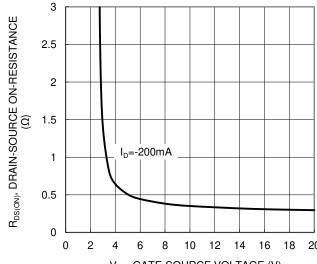


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic



 V_{GS} , GATE-SOURCE VOLTAGE (V) Figure 4. Typical Transfer Characteristic

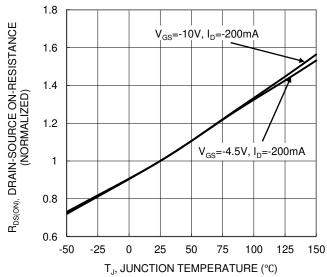


Figure 6. On-Resistance Variation with Temperature





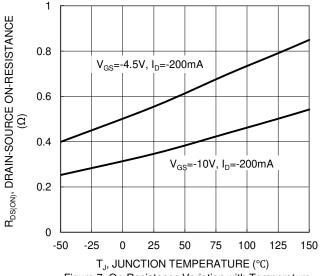
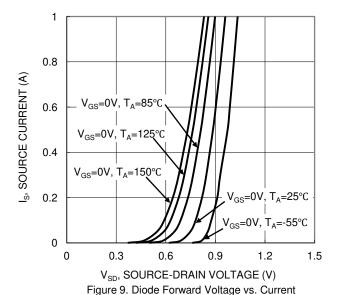


Figure 7. On-Resistance Variation with Temperature



10 8 6 $V_{GS}(V)$ V_{DS}=-10V, I_D=-200mA 4 2 0 0.2 0.4 0.6 0.8 1.2 1 1.4

 Q_g (nC) Figure 11. Gate Charge

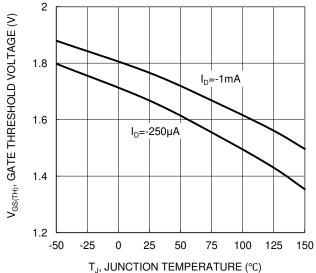


Figure 8. Gate Threshold Variation vs. Temperature

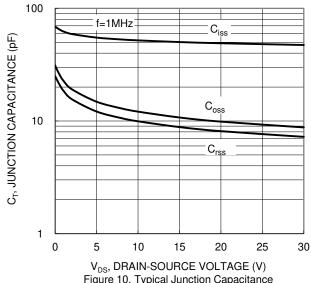


Figure 10. Typical Junction Capacitance

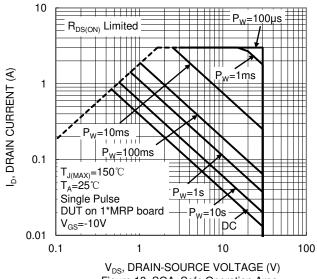
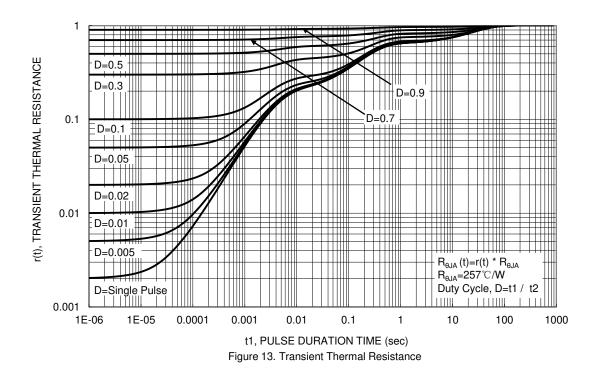


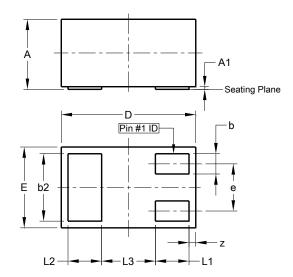
Figure 12. SOA, Safe Operation Area





Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

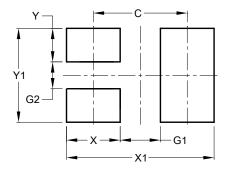


X1-DFN1006-3					
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0.00	0.05	0.03		
b	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
Е	0.55	0.675	0.60		
е	1	-	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	-	-	0.40		
Z	0.02	0.08	0.05		
All Dimensions in mm					



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Υ	0.25
Y1	0.70

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